

## N - CHANNEL ENHANCEMENT MODE PowerMESH™ MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP6NB50	500 V	< 1.5 Ω	5.8 A
STP6NB50FP	500 V	< 1.5 Ω	3.4 A

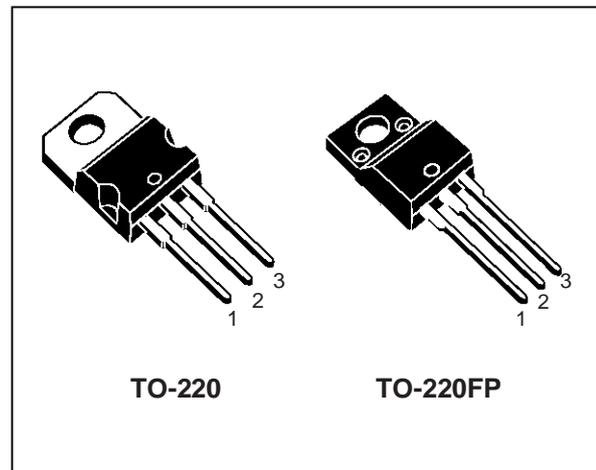
- TYPICAL R<sub>DS(on)</sub> = 1.35 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

### DESCRIPTION

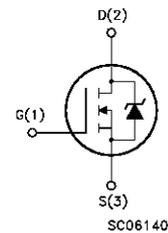
Using the latest high voltage MESH OVERLAY™ process, SGS-Thomson has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R<sub>DS(on)</sub> per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP6NB50	STP6NB50FP	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	500		V
V <sub>GS</sub>	Gate-source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	5.8	3.4	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	3.7	2.1	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	23.2	23.2	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	100	35	W
	Derating Factor	0.8	0.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.5	4.5	V/ns
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	--	2000	°C
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 6A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

# STP6NB50/FP

## THERMAL DATA

			TO-220	TO-220FP	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.25	3.57	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	5.8	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	290	mJ

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	500			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	3	4	5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 2.9 A		1.35	1.5	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	5.8			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 2.9 A	2.5	4		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		680	884	pF
C <sub>oss</sub>	Output Capacitance			110	149	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			12	16	pF

**ELECTRICAL CHARACTERISTICS** (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 250\text{ V}$ $I_D = 2.9\text{ A}$		11.5	16	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		8	12	ns
$Q_g$	Total Gate Charge	$V_{DD} = 400\text{ V}$ $I_D = 5.8\text{ A}$ $V_{GS} = 10\text{ V}$		21	30	nC
$Q_{gs}$	Gate-Source Charge			7.2		nC
$Q_{gd}$	Gate-Drain Charge			8		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 400\text{ V}$ $I_D = 5.8\text{ A}$		7	12	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		5	10	ns
$t_c$	Cross-over Time			15	23	ns

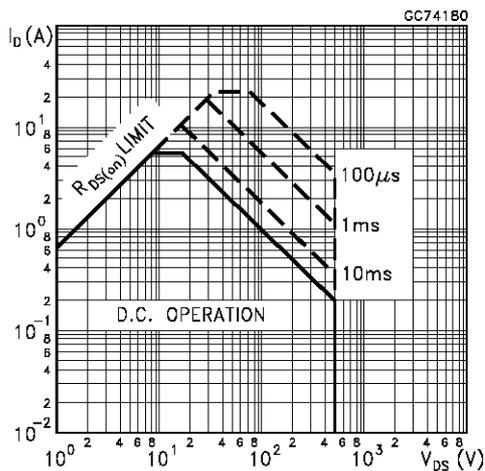
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				5.8	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				23.2	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 5.8\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 5.8\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		435		ns
$Q_{rr}$	Reverse Recovery Charge			3.3		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			15		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

Safe Operating Area for TO-220



Safe Operating Area for TO-220FP

